

TOSHIBA Photocoupler Photorelay

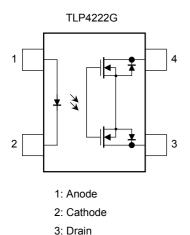
TLP4222G,TLP4222G-2

Telecommunication Measurement Equipment Security Equipment FA

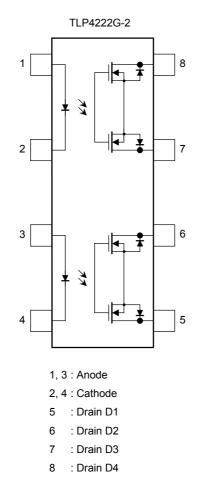
The Toshiba TLP4222G consists of an aluminum gallium arsenide infrared emitting diode optically coupled to a photo-MOSFET and is the normally closed photorelay with 350-V withstanding voltage.

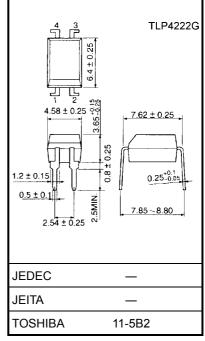
- Normally closed device
- Peak off-state voltage: 350 V (min)
- Trigger LED current: 3 mA (max)
- On-state current: 100 mA (max)
- On-state resistance: 50 Ω (max)
- Isolation voltage: 2500 Vrms (min)

Pin Configuration (top view)

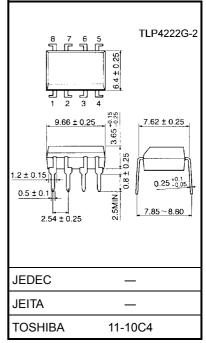


4: Drain









Weight: 0.54 g (typ.)

Unit: mm

Maximum Ratings (Ta = 25°C)

	Ch	Symbol	Rating	Unit		
	Forward current	١ _F	50	mA		
LED	Forward current derating (Ta	∆l _F /°C	-0.5	mA/°C		
	Peak forward current (100 μs	pulse, 100 pps)		I _{FP}	1	А
	Reverse voltage	V _R	5	V		
	Junction temperature		Тj	125	°C	
	Off-state output terminal volta	V _{OFF}	350	V		
	On-state current	TLP4222G				
		TLP4222G-2	One channel operation	I _{ON}	100	mA
Detector			Two channel operations			
Dete	On-state current derating (Ta ≧ 25°C)	TLP4222G				
			One channel operation	∆l _{ON} /°C	-1.0	mA/°C
		TLP4222G-2	Two channel operations			
	Junction temperature			Tj	125	°C
Stor	age temperature range	T _{stg}	-55 to 125	°C		
Ope	rating temperature range	T _{opr}	-40 to 85	°C		
Lead	d soldering temperature (10 s)	T _{sol}	260	°C		
Isola	ation voltage (AC, 1 min, R.H. \leq	BVS	2500	Vrms		

Note 1: For TLP4222G, Pins 1 and 2 are shorted together, and pins 3 and 4 are shorted together. For TLP4222G-2, Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.

Recommended Operating Conditions

Characteristics	Symbol	Min	Тур.	Max	Unit
Supply voltage	V _{DD}	_	_	280	V
Forward current	١ _F	5	_	25	mA
On-state current	I _{ON}	_	_	100	mA
Operating temperature	T _{opr}	-20		65	°C

Electrical Characteristics (Ta = 25°C)

	Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
LED	Forward voltage	VF	I _F = 10 mA	1.0	1.15	1.3	V
	Reverse current	Ι _R	V _R = 5 V	_	_	10	μA
	Capacitance	CT	V = 0, f = 1 MHz	_	30	_	pF
Detector	Off-state current	I _{OFF}	$V_{OFF} = 350 \text{ V}, I_F = 5 \text{ mA}$		_	1	μA
	Capacitance	C _{OFF}	$V = 0, f = 1 MHz, I_F = 5 mA$		30	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Trigger LED current	I _{FC}	$I_{OFF} = 10 \ \mu A$	_	1	3	mA
Return LED current	I _{FT}	I _{ON} = 100 mA	0.1	_	_	mA
On-state resistance	R _{ON}	I _{ON} = 100 mA		30	50	Ω

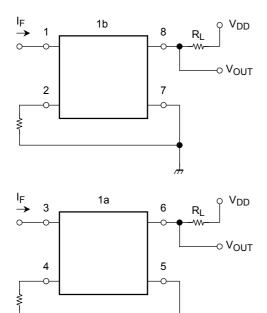
Isolation Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance input to output	CS	$V_{S} = 0, f = 1 MHz$		0.8	_	pF
Isolation resistance	R _S	$V_{S} = 500 \text{ V}, \text{ R.H.} \le 60\%$	5×10^{10}	10 ¹⁴	_	Ω
	BVS	AC, 1 min	2500	_	_	Vrms
Isolation voltage		AC, 1 s, in oil		5000	_	VIIIIS
		DC, 1 min, in oil	_	5000		Vdc

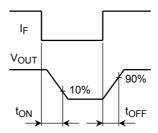
Switching Characteristics (Ta = 25°C)

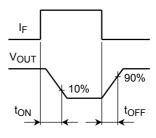
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Turn-on time	t _{ON}	$R_L = 200 \Omega$	_	0.25	0.5	ms
Turn-off time	tOFF	$V_{DD} = 20 \text{ V}, \text{ I}_{\text{F}} = 5 \text{ mA}$ (Note 2)	_	0.5	1	ms

Note 2: Switching time test circuit

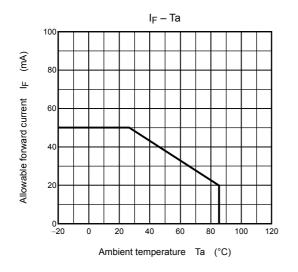


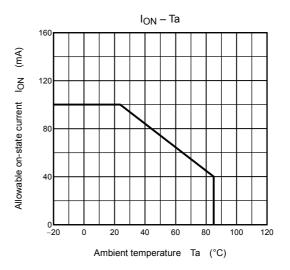
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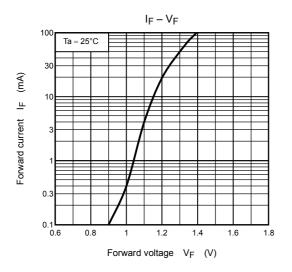




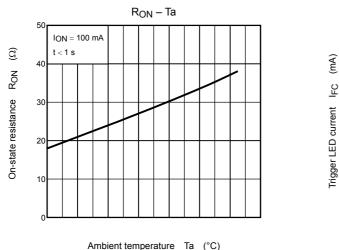
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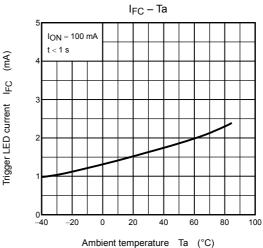


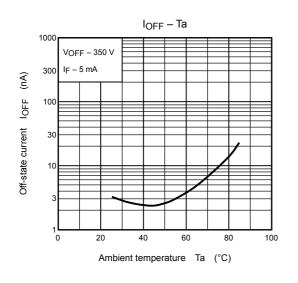


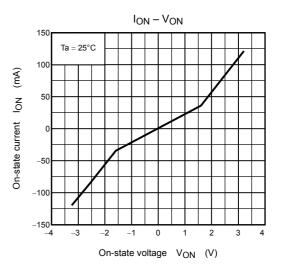


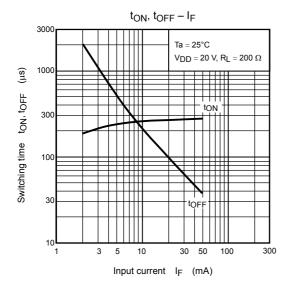
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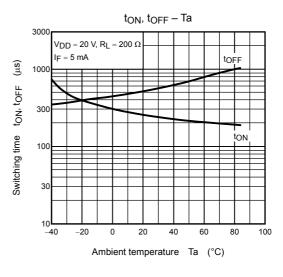












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